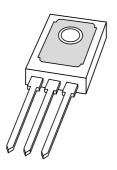
DISCRETE SEMICONDUCTORS

DATA SHEET



BD136; BD138; BD140 PNP power transistors

Product specification Supersedes data of 1997 Mar 26 1999 Apr 12





PNP power transistors

BD136; BD138; BD140

FEATURES

- High current (max. 1.5 A)
- Low voltage (max. 80 V).

APPLICATIONS

• General purpose power applications, e.g. driver stages in hi-fi amplifiers and television circuits.

DESCRIPTION

PNP power transistor in a TO-126; SOT32 plastic package. NPN complements: BD135, BD137 and BD139.

PINNING

PIN	DESCRIPTION			
1	emitter			
2	collector, connected to metal part of mounting surface			
3	base			

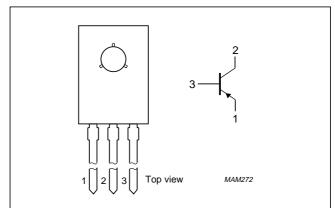


Fig.1 Simplified outline (TO-126; SOT32) and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter			
	BD136		_	-45	V
	BD138		_	-60	V
	BD140		_	-100	V
V _{CEO}	collector-emitter voltage	open base			
	BD136		_	-45	V
	BD138		_	-60	V
	BD140		_	-80	V
V _{EBO}	emitter-base voltage	open collector	_	- 5	V
I _C	collector current (DC)		_	-1.5	А
I _{CM}	peak collector current		_	-2	А
I _{BM}	peak base current		_	-1	А
P _{tot}	total power dissipation	T _{mb} ≤ 70 °C	_	8	W
T _{stg}	storage temperature		-65	+150	°C
T _j	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

PNP power transistors

BD136; BD138; BD140

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	note 1	100	K/W
R _{th j-mb}	thermal resistance from junction to mounting base		10	K/W

Note

1. Refer to TO-126 (SOT32) standard mounting conditions.

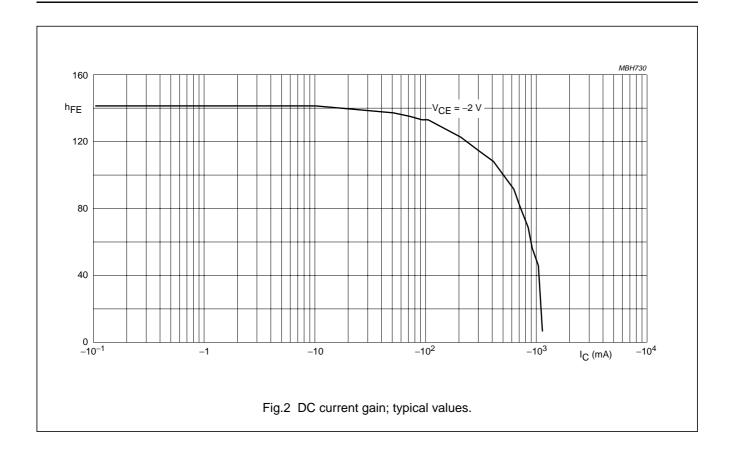
CHARACTERISTICS

 T_j = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector cut-off current	$I_E = 0; V_{CB} = -30 \text{ V}$	_	_	-100	nA
		$I_E = 0$; $V_{CB} = -30 \text{ V}$; $T_j = 125 \text{ °C}$	_	_	-10	μΑ
I _{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = -5 \text{ V}$	_	_	-100	nA
h _{FE}	DC current gain	V _{CE} = −2 V; (see Fig.2)				
		$I_C = -5 \text{ mA}$	40	_	_	
		$I_{C} = -150 \text{ mA}$	63	_	250	
		$I_{C} = -500 \text{ mA}$	25	_	_	
	DC current gain	$I_C = -150 \text{ mA}; V_{CE} = -2 \text{ V};$				
	BD136-10; BD138-10; BD140-10	(see Fig.2)	63	_	160	
	BD136-16; BD138-16; BD140-16		100	_	250	
V _{CEsat}	collector-emitter saturation voltage	$I_C = -500 \text{ mA}; I_B = -50 \text{ mA}$	_	_	-0.5	٧
V _{BE}	base-emitter voltage	$I_C = -500 \text{ mA}; V_{CE} = -2 \text{ V}$	_	_	-1	V
f _T	transition frequency	$I_C = -50 \text{ mA}; V_{CE} = -5 \text{ V};$ f = 100 MHz	_	160	_	MHz
h _{FE1} h _{FE2}	DC current gain ratio of the complementary pairs	$ I_C = 150 \text{ mA}; V_{CE} = 2 \text{ V}$	_	1.3	1.6	

PNP power transistors

BD136; BD138; BD140

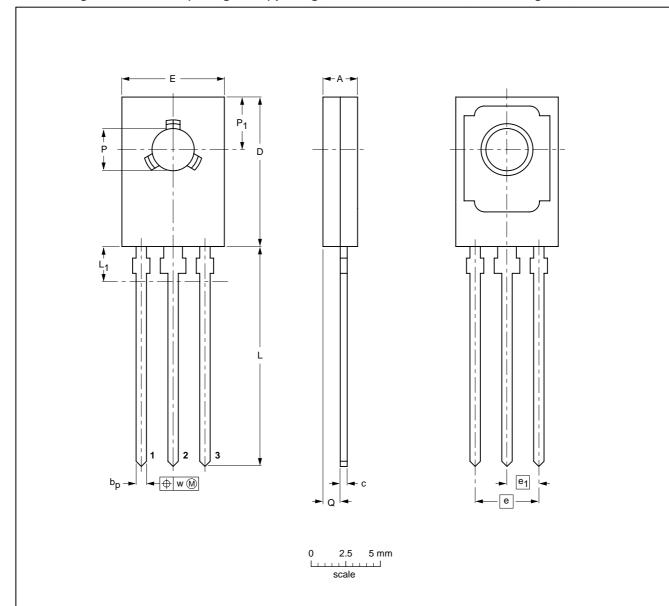


PNP power transistors

BD136; BD138; BD140

PACKAGE OUTLINE

Plastic single-ended leaded (through hole) package; mountable to heatsink, 1 mounting hole; 3 leads SOT32



DIMENSIONS (mm are the original dimensions)

UNIT	Α	bp	С	D	E	е	e ₁	L	L ₁ ⁽¹⁾ max	Q	Р	P ₁	w
mm	2.7 2.3	0.88 0.65	0.60 0.45	11.1 10.5	7.8 7.2	4.58	2.29	16.5 15.3	2.54	1.5 0.9	3.2 3.0	3.9 3.6	0.254

Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE		REFER	FERENCES EUROPEAN ISSUE			ISSUE DATE
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT32		TO-126				97-03-04

PNP power transistors

BD136; BD138; BD140

DEFINITIONS

Data Sheet Status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	

Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification

Application information

Where application information is given, it is advisory and does not form part of the specification.

is not implied. Exposure to limiting values for extended periods may affect device reliability.

LIFE SUPPORT APPLICATIONS

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